

## Vishay General Semiconductor

## **Dual High-Voltage Trench MOS Barrier Schottky Rectifier**

Ultra Low  $V_F = 0.372 \text{ V}$  at  $I_F = 5 \text{ A}$ 



**PRIMARY CHARACTERISTICS** 

 $I_{F(AV)}$ 

 $V_{\mathsf{RRM}}$ 

 $I_{FSM}$ 

 $V_F$  at  $I_F = 20 A$ 

T<sub>.I</sub> max.

TMBS®	
	1 3
TO-247AD (TO	D-3P)
PIN 1 O	PIN 2
PIN 3 O	CASE

2 x 20 A

100 V

300 A

0.60 V

150 °C

#### **FEATURES**





· Low forward voltage drop, low power losses



· High efficiency operation

· Low thermal resistance

Solder dip 260 °C, 40 s

· Component in accordance to RoHS 2002/95/EC and WEEE 2002/96/EC

### **TYPICAL APPLICATIONS**

For use in high frequency inverters, switching power supplies, freewheeling diodes, OR-ing diode, dc-to-dc converters and reverse battery protection.

## **MECHANICAL DATA**

Case: TO-247AD (TO-3P)

Epoxy meets UL 94V-0 flammability rating

Terminals: Matte tin plated leads, solderable per

J-STD-002 and JESD22-B102

E3 suffix for commercial grade, meets JESD 201 class

1A whisker test Polarity: As marked

Mounting Torque: 10 in-lbs maximum

MAXIMUM RATINGS (T <sub>A</sub> = 25 °C unless otherwise noted)				
PARAMETER		SYMBOL	V40100P	UNIT
Maximum repetitive peak reverse voltage		V <sub>RRM</sub>	100	V
Maximum average forward rectified current (Fig. 1)	per device per diode	I <sub>F(AV)</sub>	40 20	А
Peak forward surge current 8.3 ms single half sine-wave superimposed on rated load	per diode	I <sub>FSM</sub>	300	А
Peak repetitive reverse current per diode at $t_p$ = 2 $\mu$ s, 1 k	кНz	I <sub>RRM</sub>	1.0	А
Voltage rate of change (rated V <sub>R</sub> )		dV/dt	10 000	V
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>STG</sub>	- 40 to + 150	°C

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<b>ELECTRICAL CHARACTERISTICS</b> (T <sub>A</sub> = 25 °C unless otherwise noted)						
PARAMETER	TEST CONDITIONS		SYMBOL	TYP.	MAX.	UNIT
Breakdown voltage	I <sub>R</sub> = 1.0 mA	T <sub>J</sub> = 25 °C	$V_{BR}$	100	-	V
Instantaneous forward voltage per diode <sup>(1)</sup>	$I_F = 5 A$ $I_F = 10 A$ $I_F = 20 A$	T <sub>J</sub> = 25 °C	V <sub>F</sub>	0.461 0.525 0.652	- - 0.73	. v
	I <sub>F</sub> = 5 A I <sub>F</sub> = 10 A I <sub>F</sub> = 20 A	T <sub>J</sub> = 125 °C		0.372 0.443 0.595	- - 0.67	
Reverse current per diode (2)	V <sub>R</sub> = 70 V	T <sub>J</sub> = 25 °C T <sub>J</sub> = 125 °C	I <sub>R</sub>	11.5 8.0	500 15	μA mA
	V <sub>R</sub> = 100 V	T <sub>J</sub> = 25 °C T <sub>J</sub> = 125 °C		60.6 20.2	1000 45	μA mA

#### Notes:

(1) Pulse test: 300  $\mu$ s pulse width, 1 % duty cycle

(2) Pulse test: Pulse width ≤ 40 ms

THERMAL CHARACTERISTICS (T <sub>A</sub> = 25 °C unless otherwise noted)				
PARAMETER	SYMBOL	SYMBOL V40100P		
Typical thermal resistance per diode	$R_{ heta JC}$	1.5	°C/W	

ORDERING INFORMATION (Example)						
PREFERRED P/N	UNIT WEIGHT (g)	PREFERRED PACKAGE CODE	BASE QUANTITY	DELIVERY MODE		
V40100P-E3/45	6.056	45	30/tube	Tube		

#### **RATINGS AND CHARACTERISTICS CURVES**

(T<sub>A</sub> = 25 °C unless otherwise noted)

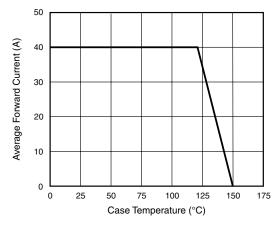


Figure 1. Forward Current Derating Curve

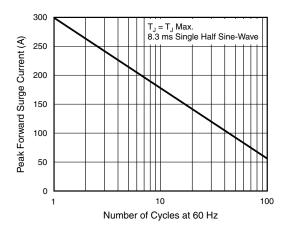


Figure 2. Maximum Non-Repetitive Peak Forward Surge Current Per Diode



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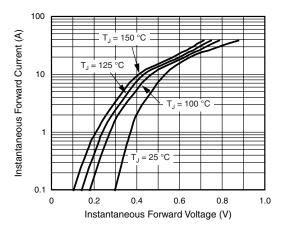


Figure 3. Typical Instantaneous Forward Characteristics Per Diode

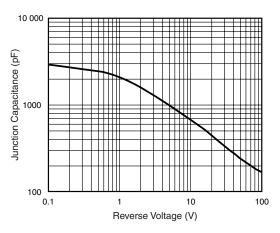


Figure 5. Typical Junction Capacitance Per Diode

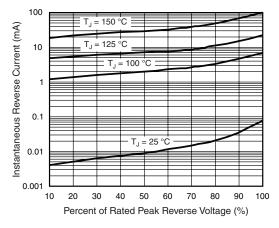


Figure 4. Typical Reverse Characteristics Per Diode

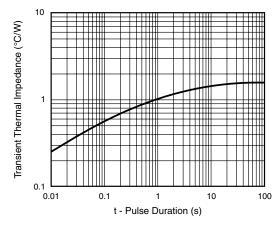
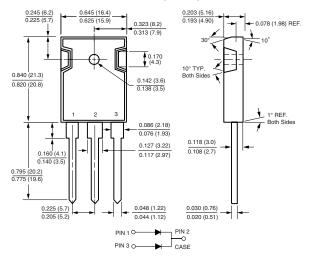


Figure 6. Typical Transient Thermal Impedance Per Diode

#### **PACKAGE OUTLINE DIMENSIONS** in inches (millimeters)

#### TO-247AD (TO-3P)



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